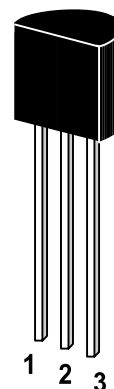


# ST 2SC732

NPN Silicon Epitaxial Planar Transistor  
for switching and AF amplifier applications.

The transistor is subdivided into two groups, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



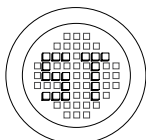
1. Emitter 2. Collector 3. Base

TO-92 Plastic Package  
Weight approx. 0.19g

## Absolute Maximum Ratings (Ta=25 °C)

|                           | Symbol    | Value       | Unit |
|---------------------------|-----------|-------------|------|
| Collector Base Voltage    | $V_{CBO}$ | 60          | V    |
| Collector Emitter Voltage | $V_{CEO}$ | 50          | V    |
| Emitter Base Voltage      | $V_{EBO}$ | 5           | V    |
| Base Current              | $I_B$     | 30          | mA   |
| Collector Current         | $I_C$     | 150         | mA   |
| Power Dissipation         | $P_{tot}$ | 400         | mW   |
| Junction Temperature      | $T_j$     | 125         | °C   |
| Storage Temperature Range | $T_s$     | -55 to +125 | °C   |

G S P FORM A IS AVAILABLE



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РАДИОТЕХ-ТРЕЙД

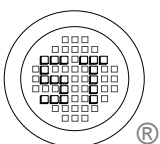
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# ST 2SC732

## Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

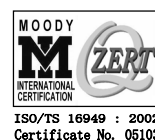
|   | Symbol                       | Min.     | Typ. | Max. | Unit          |   |
|---|------------------------------|----------|------|------|---------------|---|
| DC Current Gain<br>at $V_{CE}=6\text{V}$ , $I_C=2\text{mA}$   | Current Gain Group<br>G<br>L | $h_{FE}$ | 200  | -    | 400           | - |
|   |                              | $h_{FE}$ | 350  | -    | 700           | - |
| Base-Emitter Voltage<br>at $V_{CE}=6\text{V}$ , $I_C=2\text{mA}$  | $V_{BE}$                     | -        | 0.65 | -    | V             |   |
| Collector Cutoff Current<br>at $V_{CB}=60\text{V}$  | $I_{CBO}$                    | -        | -    | 0.1  | $\mu\text{A}$ |   |
| Emitter Cutoff Current<br>at $V_{EB}=5\text{V}$   | $I_{EBO}$                    | -        | -    | 0.1  | $\mu\text{A}$ |   |
| Collector Saturation Voltage<br>at $I_C=10\text{mA}$ , $I_B=1\text{mA}$                                 | $V_{CE(sat)}$                | -        | -    | 0.3  | V             |   |
| Gain Bandwidth Product<br>at $V_{CE}=6\text{V}$ , $I_C=1\text{mA}$                                      | $f_T$                        | -        | 150  | -    | MHz           |   |
| Output Capacitance<br>at $V_{CB}=10\text{V}$ , $f=1\text{MHz}$  | $C_{OB}$                     | -        | 2    | -    | pF            |   |
| Noise Figure<br>at $V_{CE}=6\text{V}$ , $I_C=0.1\text{mA}$<br>$f=100\text{Hz}$ , $R_G=10\text{K}\Omega$ | NF(1)                        | -        | 0.5  | 6    | V             |   |
| Noise Figure<br>at $V_{CE}=6\text{V}$ , $I_C=0.1\text{mA}$<br>$f=1\text{KHz}$ , $R_G=10\text{K}\Omega$  | NF(2)                        | -        | 0.2  | 3    | V             |   |

G S P FORM A IS AVAILABLE



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(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002  
Certificate No. 05103



ISO 14001  
Certificate No. 7116



ISO 9001 : 2000  
Certificate No. 000-199-01-002-001

Dated : 07/12/2002